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U.S. PATENT DOCUMENTS

*EXAMINER INITIAL	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
	6,294,442	9/2001	Kamal			
	5,683,935	11/1997	Miyamoto et al.			
	5,385,863	1/1995	Tatsumi et al.			
	4,755,476	7/1988	Bohm et al.			
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	5,744,824 6,114,722	04/1998 09/2000	Kousai et al. Jan et al.			

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OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)

Becker et al., LOW RESISTANCE POLYCRYSTALLINE SILICON BY BORON OR ARSENIC IMPLANTATION AND THERMAL CRYSTALLIZATION OF AMORPHOUSLY DEPOSITED FILMS , J. Appl. Phys., Vol. 56, No. 4, 15 August 1984, pages 1233-1236

Carbone et al., "Correlation of Ellipsometric Vol. Fraction to Polysilicon Grain Size from Transmission Electron Microscopy", Sept. 1999, IEEE/SEMI Adv. Semiconductor Mfg. Conf. and Workshop, pp. 359-367.

EXAMINER

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